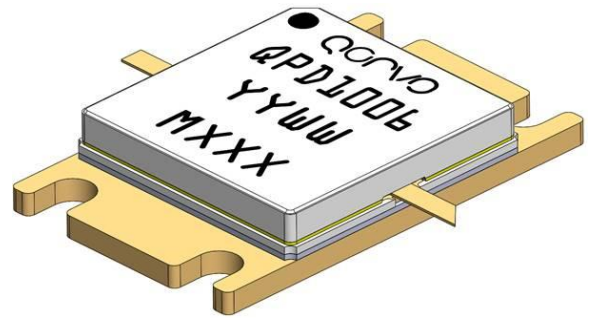


Product Overview

The QPD1006 is a 450 W (P_{3dB}) internally matched discrete GaN on SiC HEMT which operates from 1.2 to 1.4 GHz and a 50V supply rail. The device is GaN IMFET fully matched to 50 Ω in an industry standard air cavity package and is ideally suited for military and civilian radar. The device can support pulsed and CW operations.

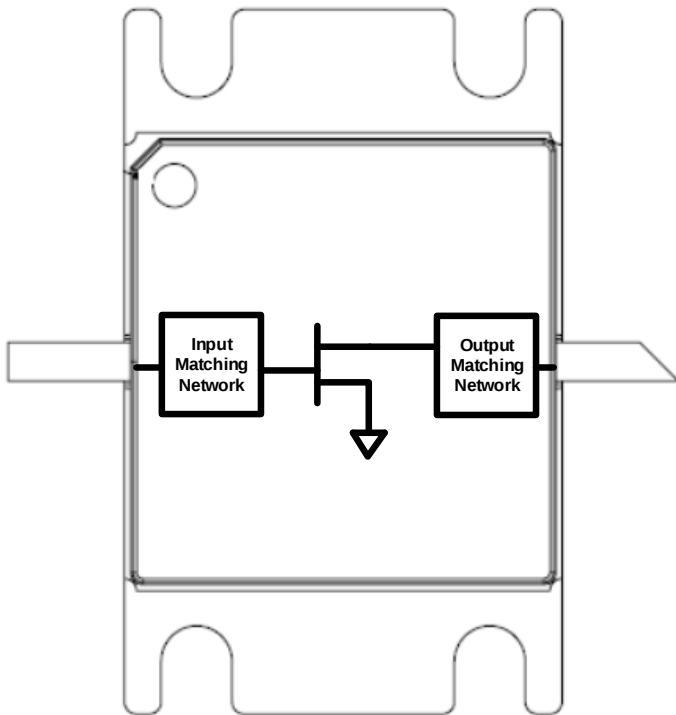
ROHS compliant.

Evaluation boards are available upon request.



NI-50CW

Functional Block Diagram



Key Features

- Frequency: 1.2 to 1.4 GHz
 - Output Power (P_{3dB})¹: 313 W (CW), 468 W (Pulsed)
 - Linear Gain¹: 17.5 dB (CW), 17.8 dB (Pulsed)
 - Typical $DEFF_{3dB}$ ¹: 55% (CW), 62.2% (Pulsed)
 - Operating Voltage: 45 V (CW), 50 V (Pulsed)
 - Low thermal resistance package
 - Pulse capable
- Note 1: @ 1.3 GHz, 25 °C

Applications

- Military radar
- Civilian radar

Part No.	Description
QPD1006	1.2 – 1.4 GHz RF IMFET
QPD1006EVB3	Evaluation Board

Absolute Maximum Ratings¹

Parameter	Rating	Units
Breakdown Voltage, BV_{DG}	+145	V
Gate Voltage Range, V_G	-7 to +2	V
Drain Current	60	A
Gate Current Range, I_G	See page 4.	mA
Power Dissipation, 10% DC 1 mS PW, P_{DISS}	496	W
RF Input Power, 10% DC 1 mS PW, 1.3 GHz, $T = 25^\circ\text{C}$	+46	dBm
Mounting Temperature (30 Seconds)	320	$^\circ\text{C}$
Storage Temperature	-65 to +150	$^\circ\text{C}$

Notes:

- Operation of this device outside the parameter ranges given above may cause permanent damage.

Recommended Operating Conditions¹

Parameter	Min	Typ	Max	Units
Operating Temp. Range	-40	+25	+85	$^\circ\text{C}$
Drain Voltage Range, V_D	+28	+50	+55	V
Drain Bias Current, I_{DQ}	–	750	–	mA
Drain Current, I_D	–	14	–	A
Gate Voltage, V_G ⁴	–	-2.7	–	V
Power Dissipation, Pulsed (P_D) ^{2, 3}	–	–	445	W
Power Dissipation, CW (P_D) ²	–	–	299	W

Notes:

- Electrical performance is measured under conditions noted in the electrical specifications table. Specifications are not guaranteed over all recommended operating conditions.
- Package base at 85°C .
- Pulse Width = 300 μs , Duty Cycle = 30%.
- To be adjusted to desired I_{DQ} .

RF Characterization – EVB CW Performance At 1.2 GHz¹

Parameter	Min	Typ	Max	Units
Linear Gain, G_{LIN}	–	17.5	–	dB
Output Power at 3dB compression point, P_{3dB}	–	55.4	–	dBm
Drain Efficiency at 3dB compression point, $DEFF_{3dB}$	–	56.2	–	%
Gain at 3dB compression point, G_{3dB}	–	14.5	–	dB

Notes:

- $V_D = +45\text{ V}$, $I_{DQ} = 750\text{ mA}$, $T_A = 25^\circ\text{C}$

RF Characterization – EVB CW Performance At 1.3 GHz¹

Parameter	Min	Typ	Max	Units
Linear Gain, G_{LIN}	–	17.3	–	dB
Output Power at 3dB compression point, P_{3dB}	–	54.9	–	dBm
Drain Efficiency at 3dB compression point, $DEFF_{3dB}$	–	54.6	–	%
Gain at 3dB compression point, G_{3dB}	–	14.3	–	dB

Notes:

- $V_D = +45\text{ V}$, $I_{DQ} = 750\text{ mA}$, $T_A = 25^\circ\text{C}$

RF Characterization – EVB CW Performance At 1.4 GHz¹

Parameter	Min	Typ	Max	Units
Linear Gain, G_{LIN}	–	17.5	–	dB
Output Power at 3dB compression point, P_{3dB}	–	54.7	–	dBm
Drain Efficiency at 3dB compression point, $DEFF_{3dB}$	–	49.4	–	%
Gain at 3dB compression point, G_{3dB}	–	14.5	–	dB

Notes:

- $V_D = +45\text{ V}$, $I_{DQ} = 750\text{ mA}$, $T_A = 25^\circ\text{C}$

RF Characterization – EVB Pulsed Performance At 1.2 GHz¹

Parameter	Min	Typ	Max	Units
Linear Gain, G_{LIN}	–	17.8	–	dB
Output Power at 3dB compression point, P_{3dB}	–	57.1	–	dBm
Drain Efficiency at 3dB compression point, $DEFF_{3dB}$	–	62.8	–	%
Gain at 3dB compression point, G_{3dB}	–	14.8	–	dB

Notes:

2. $V_D = +50\text{ V}$, $I_{DQ} = 750\text{ mA}$, $T_A = +25\text{ }^\circ\text{C}$, $PW = 300\text{ }\mu\text{S}$, $DC = 30\%$

RF Characterization – EVB Pulsed Performance At 1.3 GHz¹

Parameter	Min	Typ	Max	Units
Linear Gain, G_{LIN}	–	17.8	–	dB
Output Power at 3dB compression point, P_{3dB}	–	56.7	–	dBm
Drain Efficiency at 3dB compression point, $DEFF_{3dB}$	–	62.0	–	%
Gain at 3dB compression point, G_{3dB}	–	14.8	–	dB

Notes:

1. $V_D = +50\text{ V}$, $I_{DQ} = 750\text{ mA}$, $T_A = +25\text{ }^\circ\text{C}$, $PW = 300\text{ }\mu\text{S}$, $DC = 30\%$

RF Characterization – EVB Pulsed Performance At 1.4 GHz¹

Parameter	Min	Typ	Max	Units
Linear Gain, G_{LIN}	–	17.8	–	dB
Output Power at 3dB compression point, P_{3dB}	–	57.1	–	dBm
Drain Efficiency at 3dB compression point, $DEFF_{3dB}$	–	59.6	–	%
Gain at 3dB compression point, G_{3dB}	–	14.8	–	dB

Notes:

1. $V_D = +50\text{ V}$, $I_{DQ} = 750\text{ mA}$, $T_A = +25\text{ }^\circ\text{C}$, $PW = 300\text{ }\mu\text{S}$, $DC = 30\%$

RF Characterization – Mismatch Ruggedness at 1.3 GHz¹

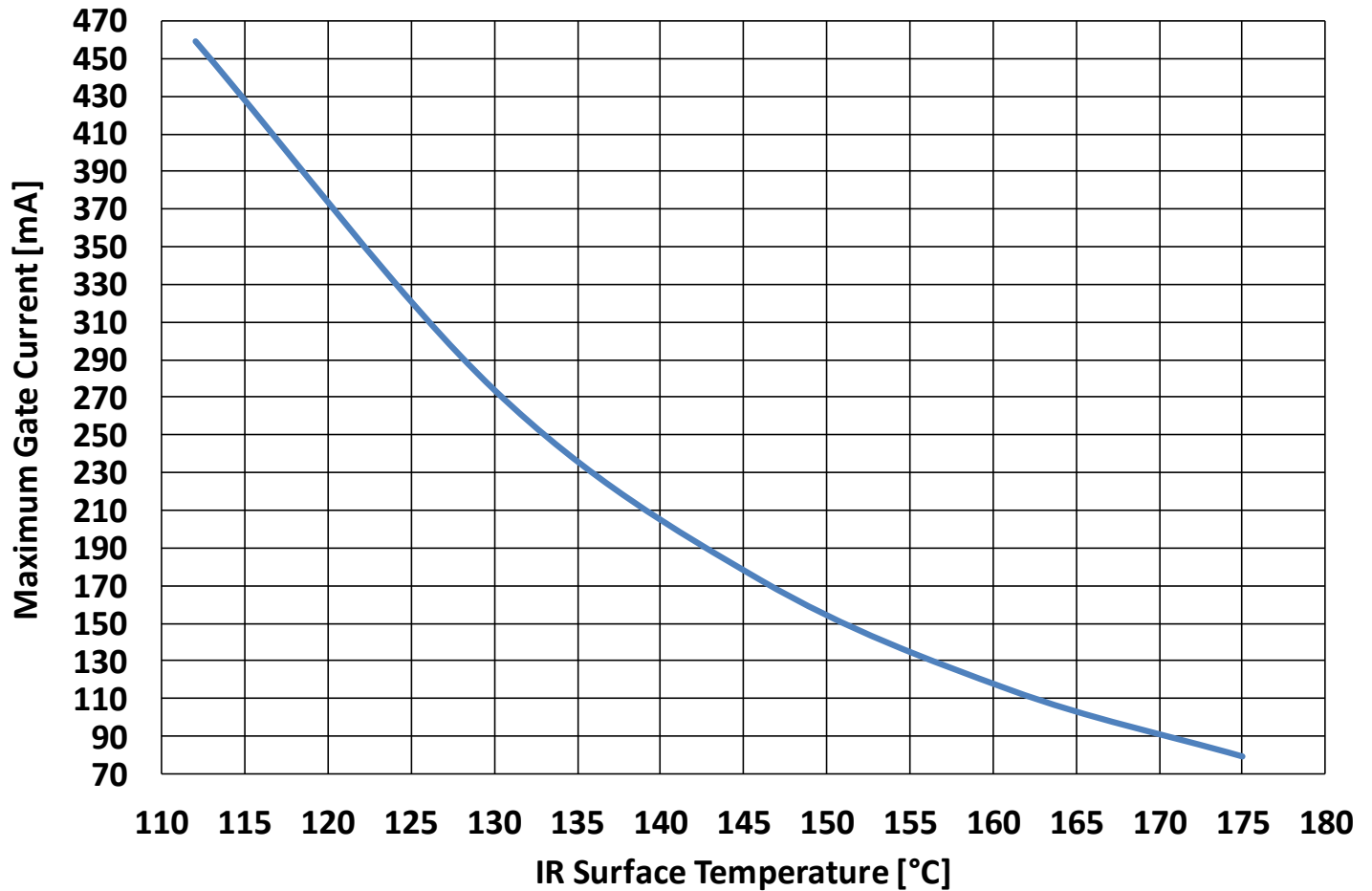
Symbol	Parameter	dB Compression	Typical
VSWR	Impedance Mismatch Ruggedness	3	10:1

Notes:

1. Test conditions unless otherwise noted: $T_A = 25\text{ }^\circ\text{C}$, $V_D = 50\text{ V}$, $I_{DQ} = 750\text{ mA}$, $100\text{ }\mu\text{S}$ PW , 10% DC
2. Driving input power is determined at pulsed compression under matched condition at EVB output connector.

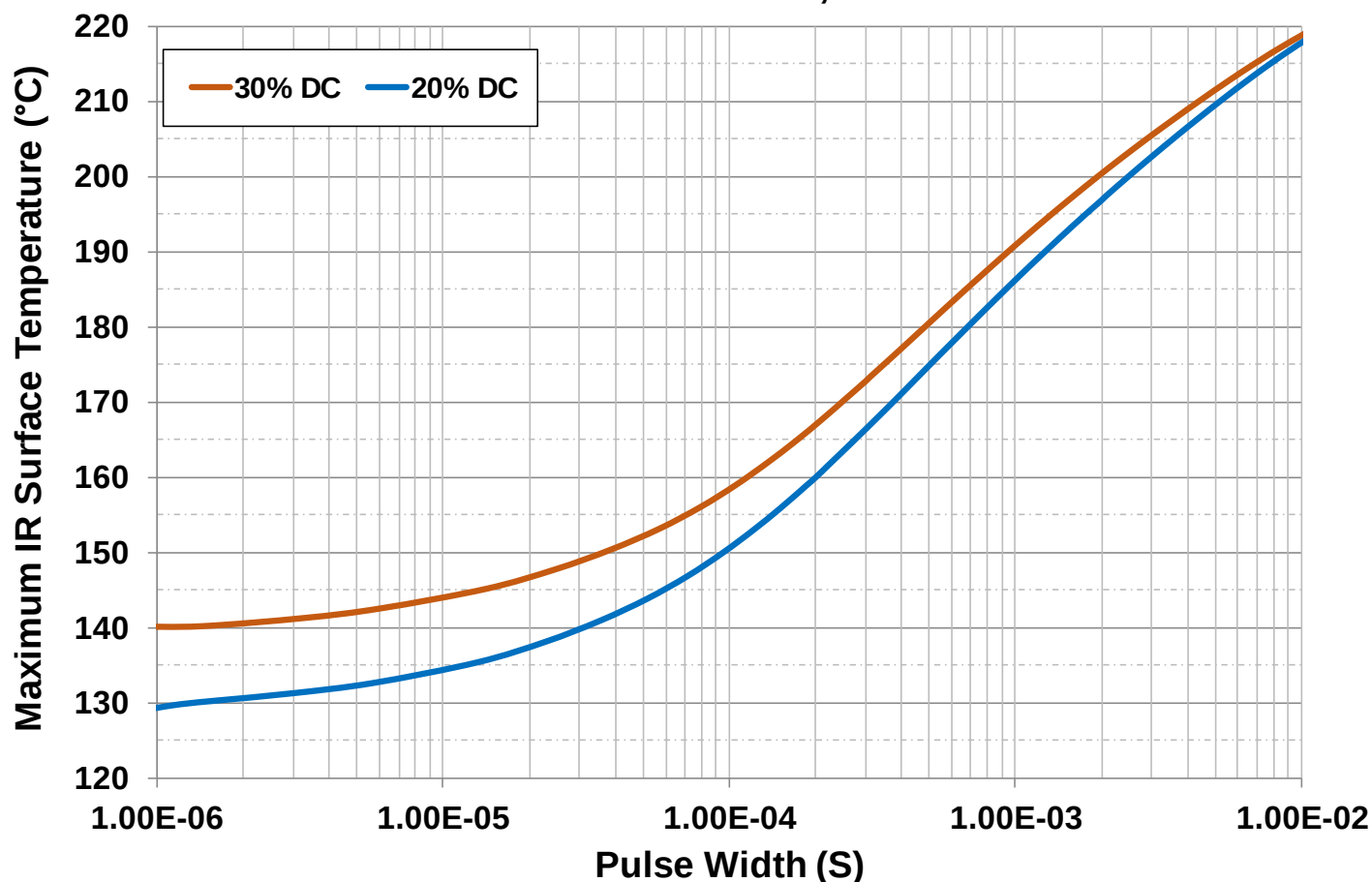
Maximum Gate Current

Maximum Gate Current Vs. IR Surface Temperature



Thermal and Reliability Information – Pulsed

Maximum IR Surface Temperature vs. Pulse Width
Back Base Fixed at 85 °C, P_{diss} = 331 W

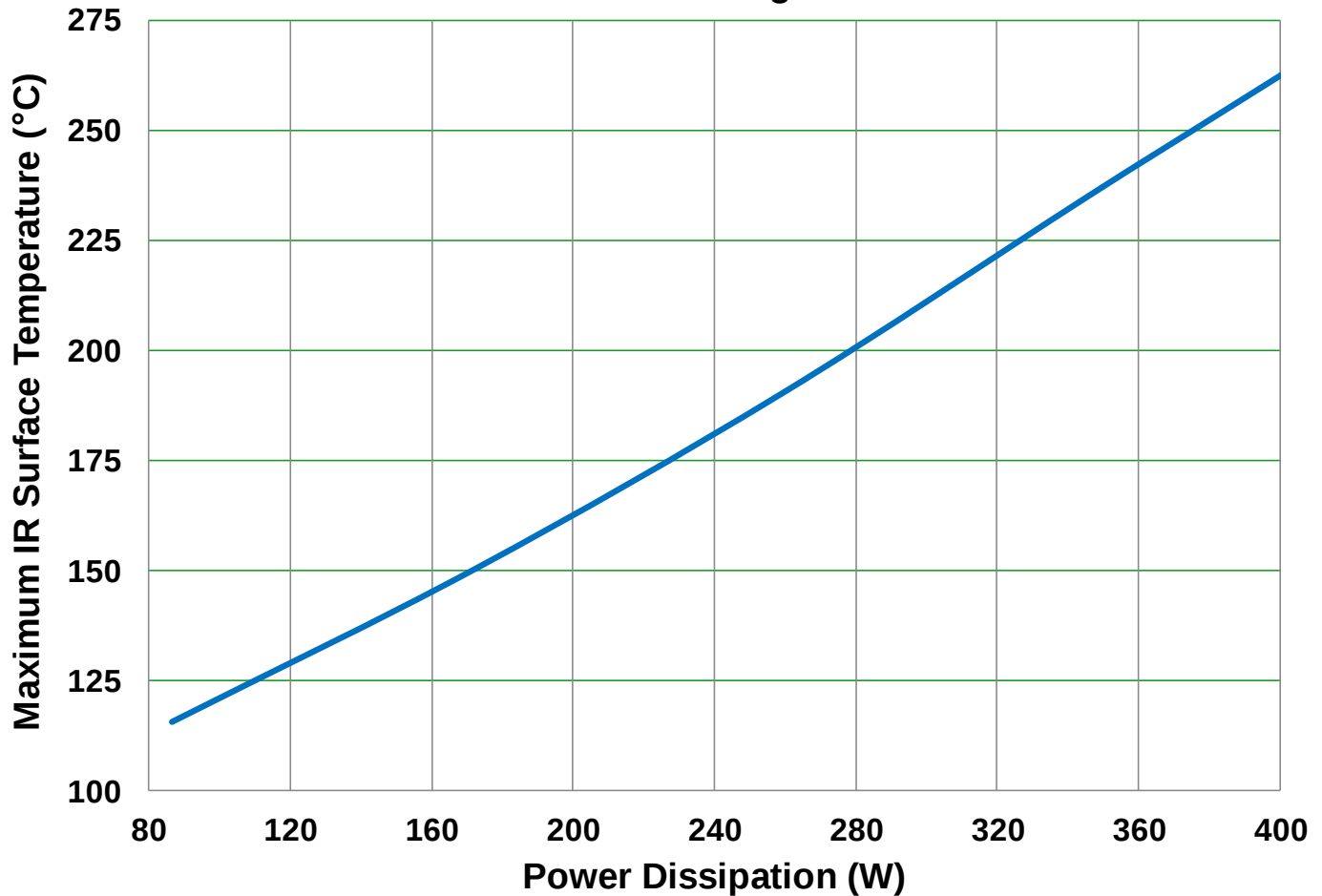


Parameter	Conditions	Values	Units
Thermal Resistance, IR ¹ (θ_{JC})	85 °C back side temperature	0.23	°C/W
Peak IR Surface Temperature ¹ (T_{CH})	331 W P _{diss} , 200 uS PW, 20% DC	160	°C
Thermal Resistance, IR ¹ (θ_{JC})	85 °C back side temperature	0.27	°C/W
Peak IR Surface Temperature ¹ (T_{CH})	331 W P _{diss} , 300 uS PW, 30% DC	173	°C

¹ Refer to the following document [GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates](#)

Thermal and Reliability Information – CW

Maximum IR Surface Temperature vs. Power Dissipation
Back Surface of Package Fixed at 85 °C



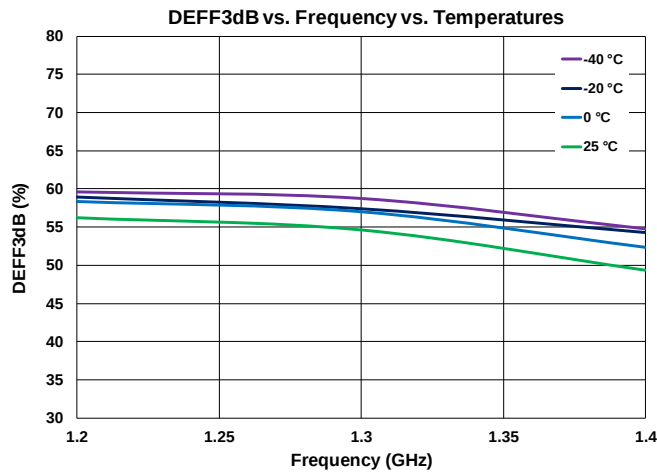
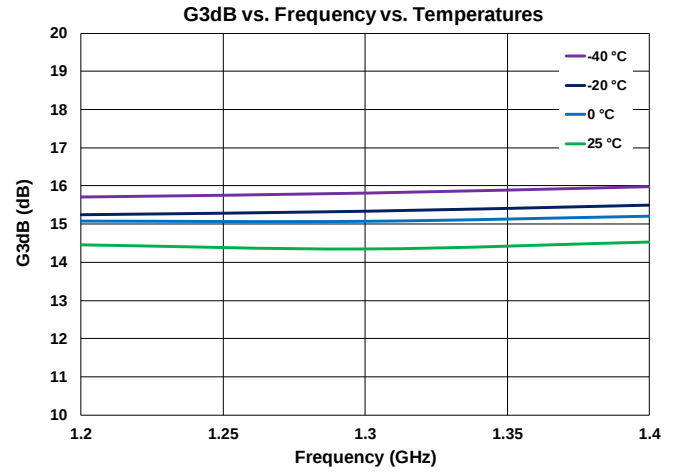
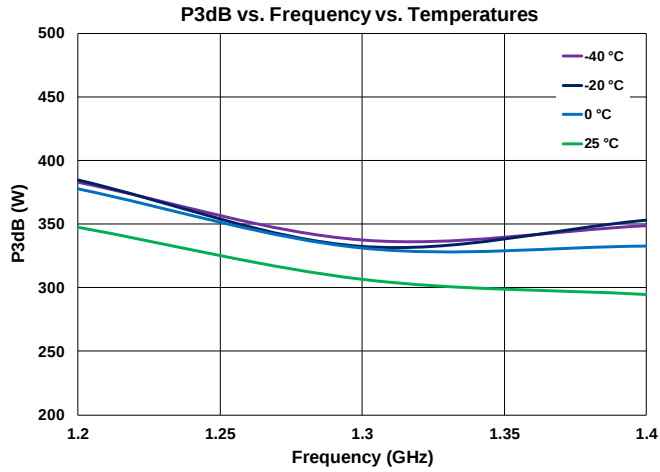
Parameter	Conditions	Values	Units
Thermal Resistance, IR ¹ (θ_{JC})	85 °C back side temperature	0.35	°C/W
Peak IR Surface Temperature ¹ (T_{CH})	86.4 W P _{diss} , CW	116	°C
Thermal Resistance, IR ¹ (θ_{JC})	85 °C back side temperature	0.38	°C/W
Peak IR Surface Temperature ¹ (T_{CH})	177.8 W P _{diss} , CW	151	°C
Thermal Resistance, IR ¹ (θ_{JC})	85 °C back side temperature	0.41	°C/W
Peak IR Surface Temperature ¹ (T_{CH})	259.2 W P _{diss} , CW	190	°C
Thermal Resistance, IR ¹ (θ_{JC})	85 °C back side temperature	0.43	°C/W
Peak IR Surface Temperature ¹ (T_{CH})	345.6 W P _{diss} , CW	235	°C

¹ Refer to the following document [GaN Device Channel Temperature, Thermal Resistance, and Reliability Estimates](#)

CW Power Drive-up Performance Over Temperatures Of 1.2 – 1.4 GHz EVB¹

Notes:

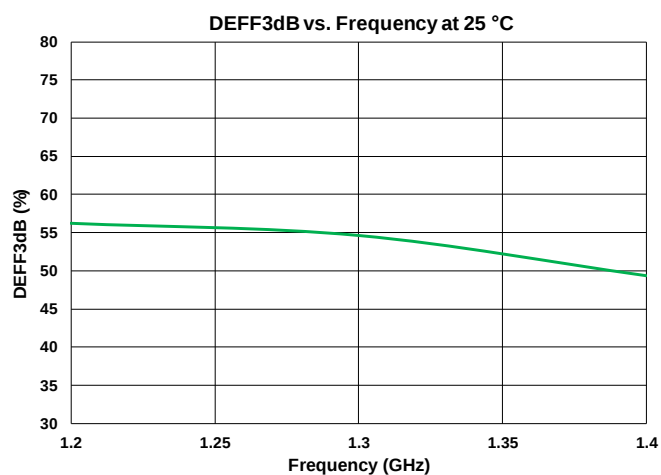
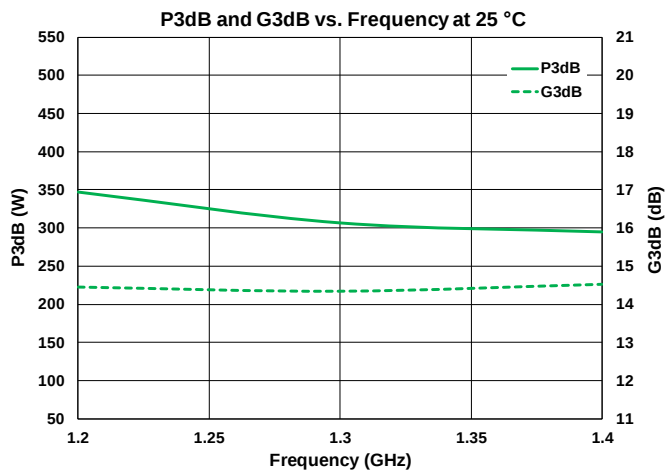
1. $V_D = 45\text{ V}$, $I_{DQ} = 750\text{ mA}$.



CW Power Drive-up Performance At 25 °C Of 1.2 – 1.4 GHz EVB¹

Notes:

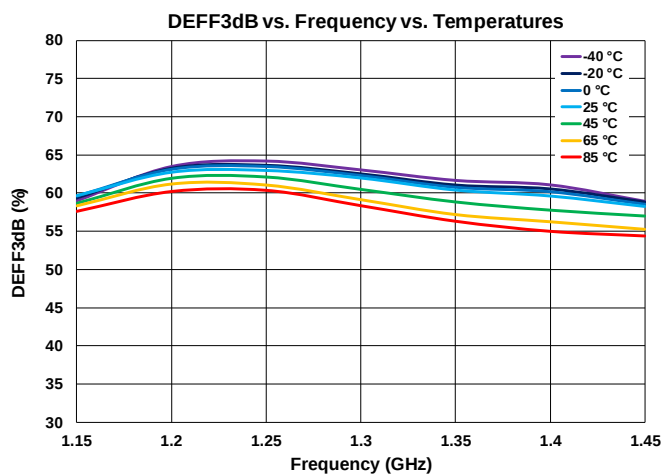
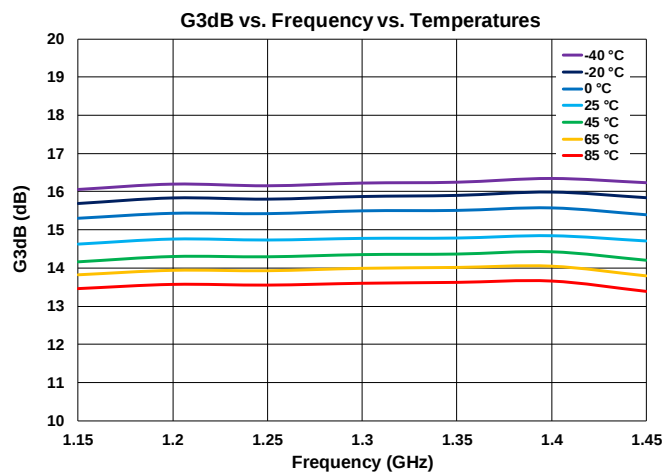
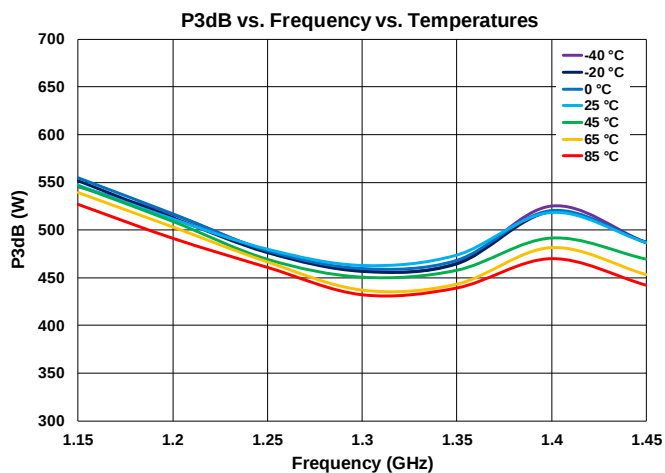
1. $V_D = 45\text{ V}$, $I_{DQ} = 750\text{ mA}$.



Pulsed Power Drive-up Performance Over Temperatures Of 1.2 – 1.4 GHz EVB¹

Notes:

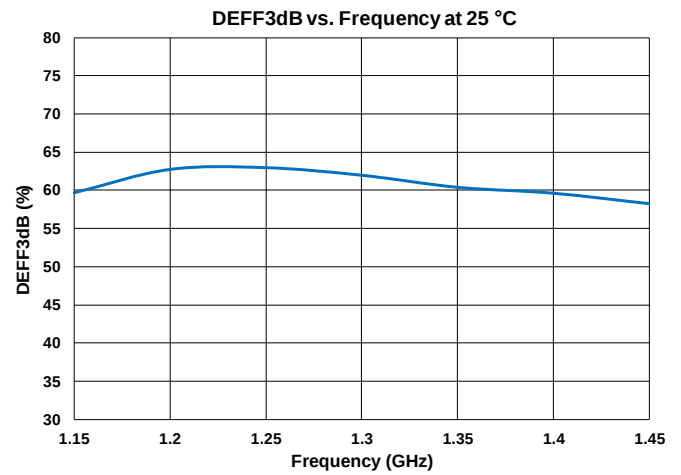
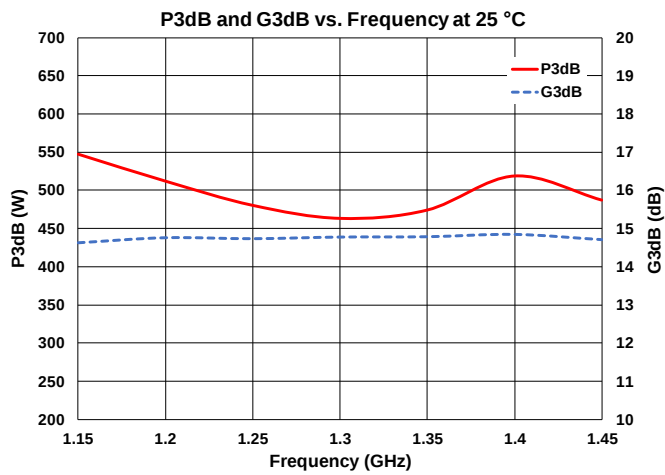
1. $V_D = 50\text{ V}$, $I_{DQ} = 750\text{ mA}$, $PW = 300\text{ }\mu\text{s}$, $DC = 30\%$.



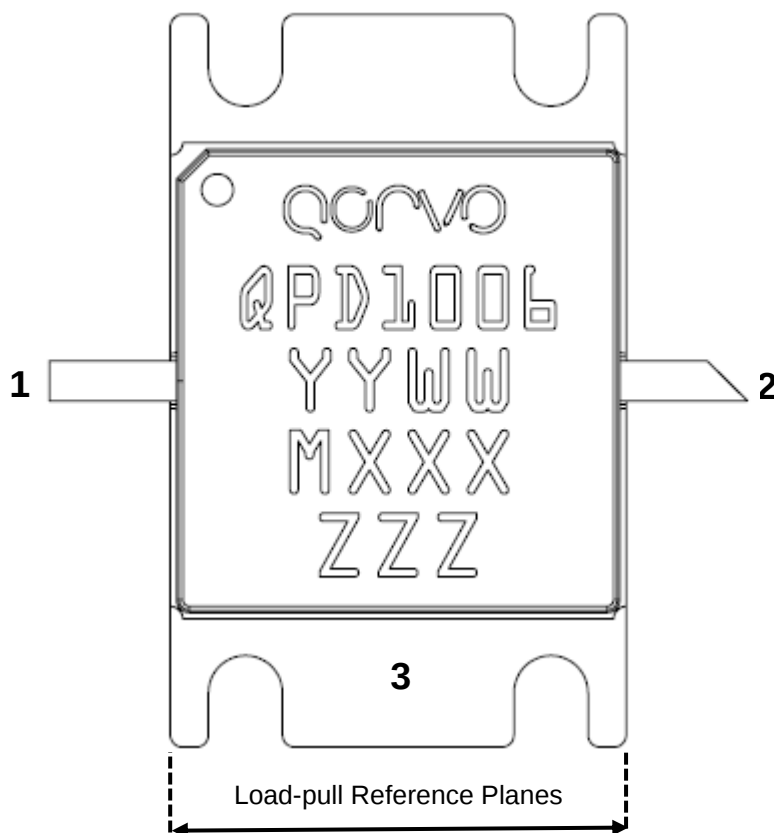
Power Drive-up Performance At 25 °C Of 1.2 – 1.4 GHz EVB¹

Notes:

1. $V_D = 50\text{ V}$, $I_{DQ} = 750\text{ mA}$, $PW = 300\text{ }\mu\text{s}$, $DC = 30\%$.



Pin Configuration and Description, and Package Marking¹



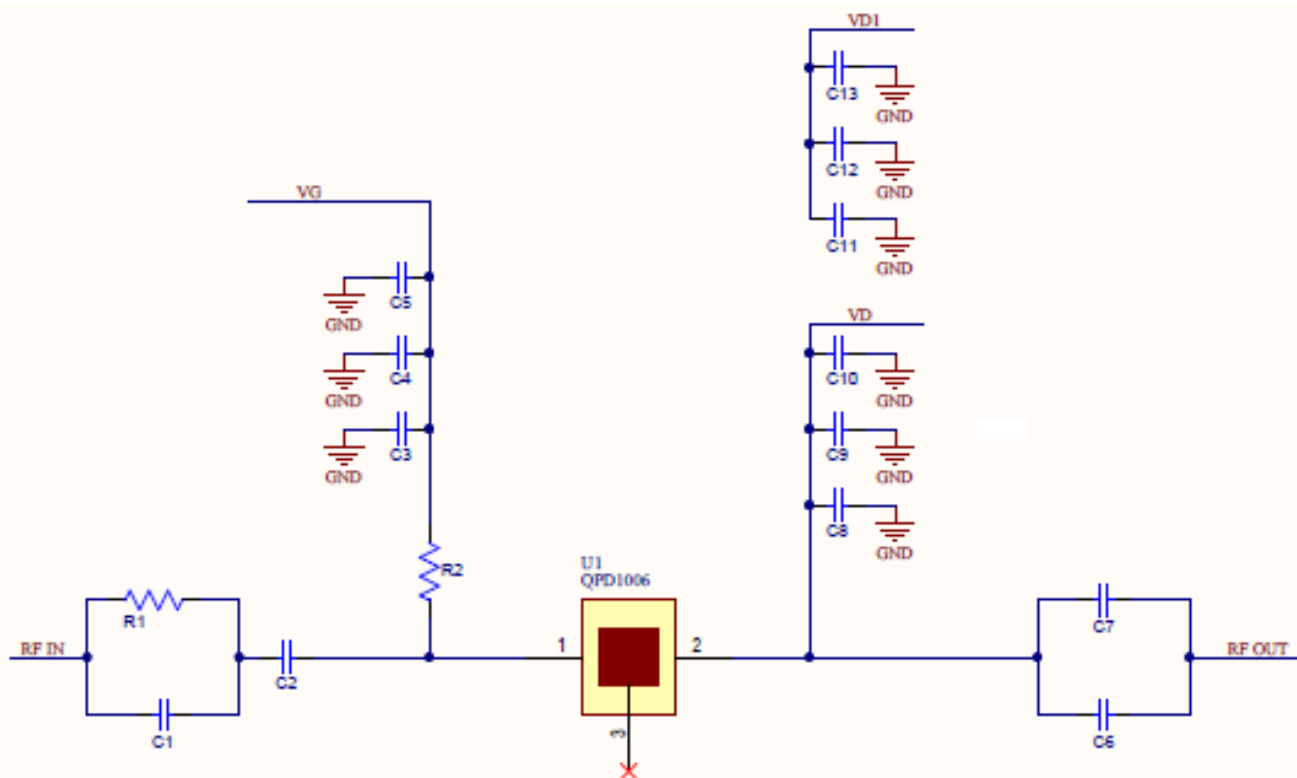
Notes:

1. The QPD1006 will be marked with the “1006” designator and a lot code marked below the part designator. The “YY” represents the last two digits of the calendar year the part was manufactured, the “WW” is the work week of the assembly lot start, the “MXXX” is the production lot number. “ZZZ” is the unique serial number.

Pin Description

Pin	Symbol	Description
1	V_G / RF IN	Gate voltage / RF Input
2	V_D / RF OUT	Drain voltage / RF Output
3	GND	Package base / Ground

Schematic – 1.2 – 1.4 GHz EVB



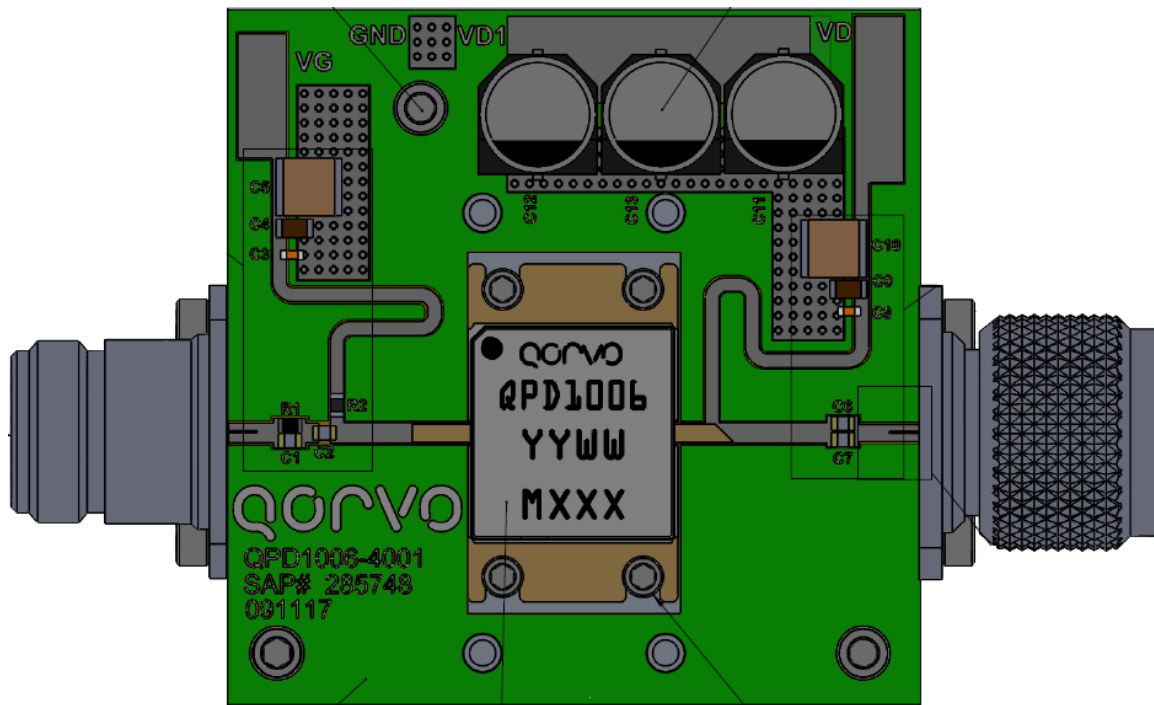
Bias-up Procedure

1. Set V_G to -4 V.
2. Set I_D current limit to 800 mA.
3. Apply 50 V V_D .
4. Slowly adjust V_G until I_D is set to 750 mA.
5. Set I_D current limit to 7 A
6. Apply RF.

Bias-down Procedure

1. Turn off RF signal.
2. Turn off V_D
3. Wait 2 seconds to allow drain capacitor to discharge
4. Turn off V_G

1.2 – 1.4 GHz EVB ^{1, 2}



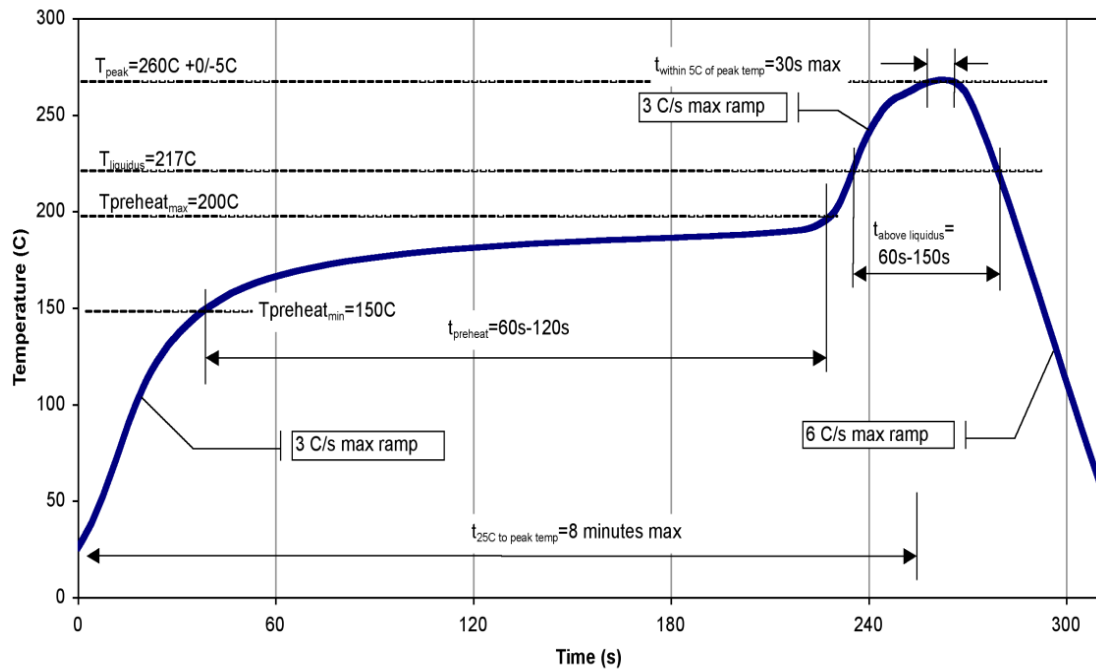
Notes:

1. PCB Material: RO4350B, 20 mil thickness, 1 oz copper cladding
2. For good pulsed operation, an additional 3300 uF, 100 V electrolytic capacitor is required on the drain supply line.

Bill Of material – 1.2 – 1.4 GHz Pulsed or CW EVB

Ref Des	Value	Qty	Manufacturer	Part Number
C1, C2, C6, C7	33 pF	4	ATC	600F330JT250XT
C4, C9	0.1 uF	2	TDK	C3216X7R2A104K160AA
C3, C8	240 pF	2	AVX	UQCFVA241JAT2A\500
C11, C12, C13	220 uF	3	United Chemicon	EMVY500ADA221MJA03
C5, C10	10 uF	2	TDK	C5750X7S2A106M230KB
R1	100 Ohm	1	Kamaya, Inc	RMC1/10-101JTP
R2	10 Ohm	1	Vishay	CRCW080510R0JNTA

Recommended Solder Temperature Profile



Handling Precautions

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	1000 V	ANSI/ESD/JEDEC JS-001
ESD – Charged Device Model (CDM)	1000 V	ANSI/ESD/JEDEC JS-002
MSL – Moisture Sensitivity Level	MSL3	IPC/JEDEC J-STD-020



Caution!
ESD-Sensitive Device

Solderability

Compatible with both lead-free (260°C max. reflow temp.) and tin/lead (245°C max. reflow temp.) soldering processes. Solder profiles available upon request.

Package lead plating is NiAu. Au thickness is 1 µm minimum.

RoHS Compliance

This part is compliant with 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment) as amended by Directive 2015/863/EU.

This product also has the following attributes:

- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C₁₅H₁₂Br₄O₂) Free
- PFOS Free
- SVHC Free

Contact Information

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Email: customer.support@qorvo.com

For technical questions and application information: Email: info-products@qorvo.com

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